MoSys , Inc. Corporate Overview

AeA Classic Financial Conference

November 4 & 5, 2008

Safe Harbor Statement

This presentation may contain forward-looking statements about the Company including, without limitation, benefits and performance expected from use of the Company's 1T-SRAM®, 1T-FLASH™, and mixed-signal technologies. Forward-looking statements are based on certain assumptions and expectations of future events that are subject to risks and uncertainties. Actual results and trends may differ materially from historical results or those projected in any such forward-looking statements depending on a variety of factors. These factors include but are not limited to, customer acceptance of our 1T-SRAM, 1T-FLASH, and mixed-signal technologies, the timing and nature of customer requests for our services under existing license agreements, the level of commercial success of licensees' products, ease of manufacturing and yields of devices incorporating our 1T-SRAM, our ability to enhance the 1T-SRAM, 1T-FLASH, and mixed-signal technology or develop new technologies, the level of intellectual property protection provided by our patents, the vigor and growth of markets served by our licensees and customers, and operations of the Company and other risks identified in the Company's most recent annual and quarterly reports on Forms 10-K and 10-Q filed with the Securities and Exchange Commission, as well as other reports that MoSys files from time to time with the Securities and Exchange Commission. MoSys undertakes no obligation to update publicly any forward-looking statement for any reason, except as required by law, even as new information becomes available or other events occur in the future.

MoSys (NDQ: MOSY) Background

1991	*2001*	*2002*	*2007*	*2007*	*2008*
Founded from IDT	***IPO (MOSY)***	***Chip to SRAM IP Focus***	***Acquired Analog/MS IP***	***Major Restructuring***	***1T-DDI 1T-FLASH Analog/MS IP***

- ❑ **World leader in SoC embedded memory IP: 1T-SRAM®**
  - 80+ customers, 175+ licenses, more than 160 million units shipped
  - 166 memory patents - 91 U.S. & 75 foreign
- ❑ **HQ in Sunnyvale, CA, ~200 employees (80% engineering)**

Global R&D Centers

- Silicon Valley
- Korea
- Shanghai
- Romania

- ❑ **Strong financial fundamentals**
  - High gross margins with recurring royalty revenue model
  - $72 million cash & investments - no debt

New MoSys Leadership Team

- **Len Perham (CEO) joined November, 2007**
  - 17 years at IDT ('83-'00), CEO from '91-'00
  - Incubated MoSys, Centaur Tech, Clear-Logic, QED, Galileo Tech

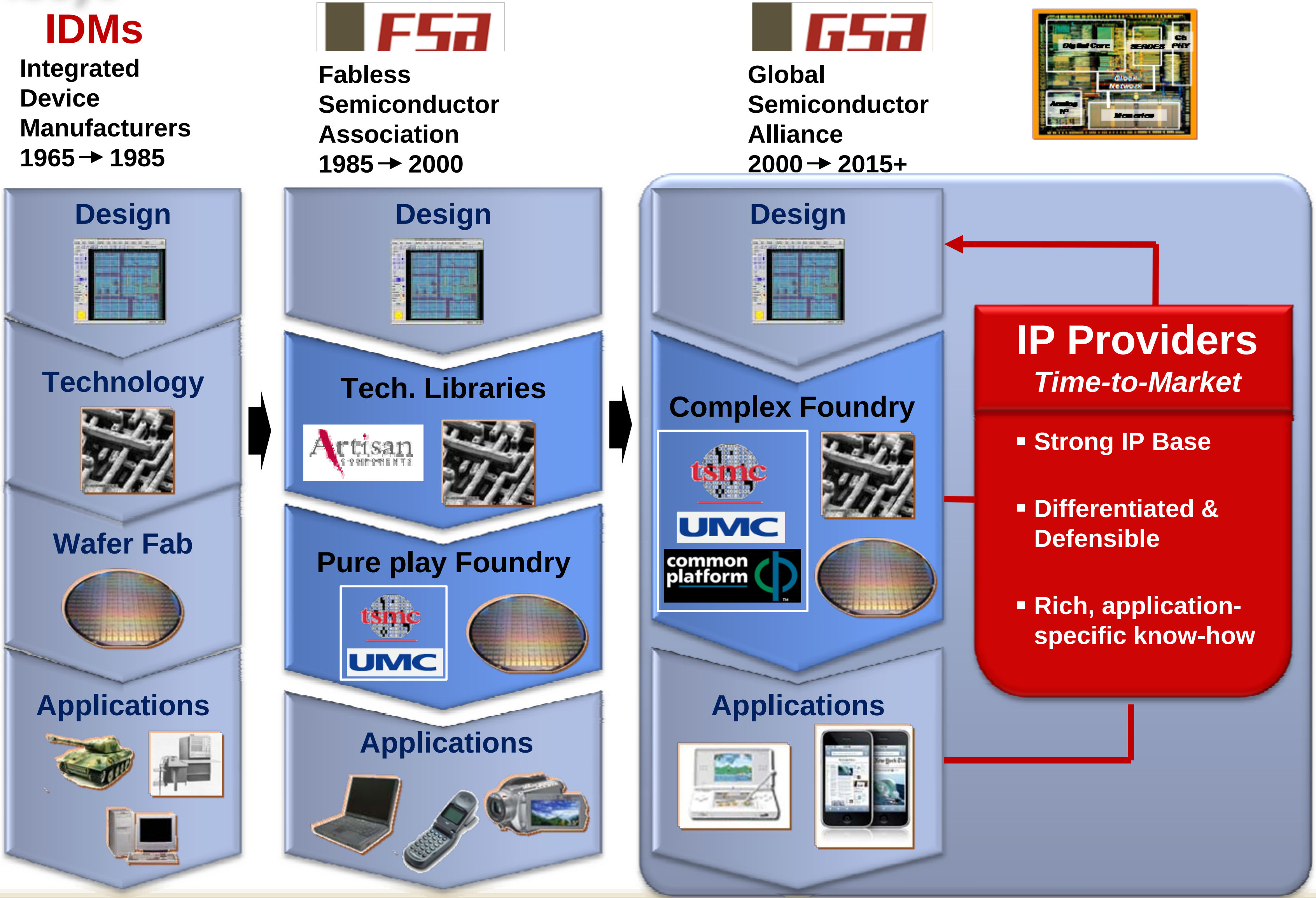
- **Strengthened Executive Team in 2008**
  - Q1 - CFO – Jim Sullivan (CFO- Apptera, 8X8 (Ndq: EGHT), Netergy)
  - Q2 - Sr. Director Foundries – John Chin (Cadence, TSMC, LSI)
  - Q3 - VP Business Operations – Dave DeMaria (Cadence, Apache, Optimal)

- **Added Key Engineering Talent**
  - Flash memory expertise
  - 40+ analog/mixed signal & firmware engineers in China
  - 50+ analog/mixed signal engineers in Romania

- **Senior Advisory Team**
  - Dr. Frank Lee – Sr. circuit design/device physics expert
  - Katherine Jen – Influential Business Leader

Mission: **Grow from Leadership in embedded 1T-SRAM into New Memory & Analog/Mixed Signal Markets**

The IP Opportunity: Next Wave of Electronics Industry Evolution



IDMs
Integrated
Device
Manufacturers
1965 → 1985

- Design
- Technology
- Wafer Fab
- Applications

Fabless
Semiconductor
Association
1985 → 2000

- Design
- Tech. Libraries
- Pure play Foundry
- Applications

Global
Semiconductor
Alliance
2000 → 2015+

- Design
- Complex Foundry
- Applications

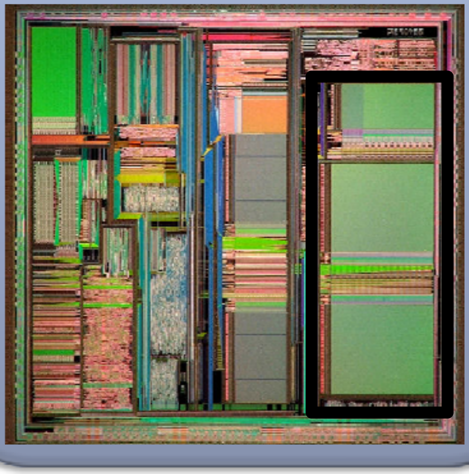
IP Providers
Time-to-Market

- Strong IP Base
- Differentiated & Defensible
- Rich, application-specific know-how

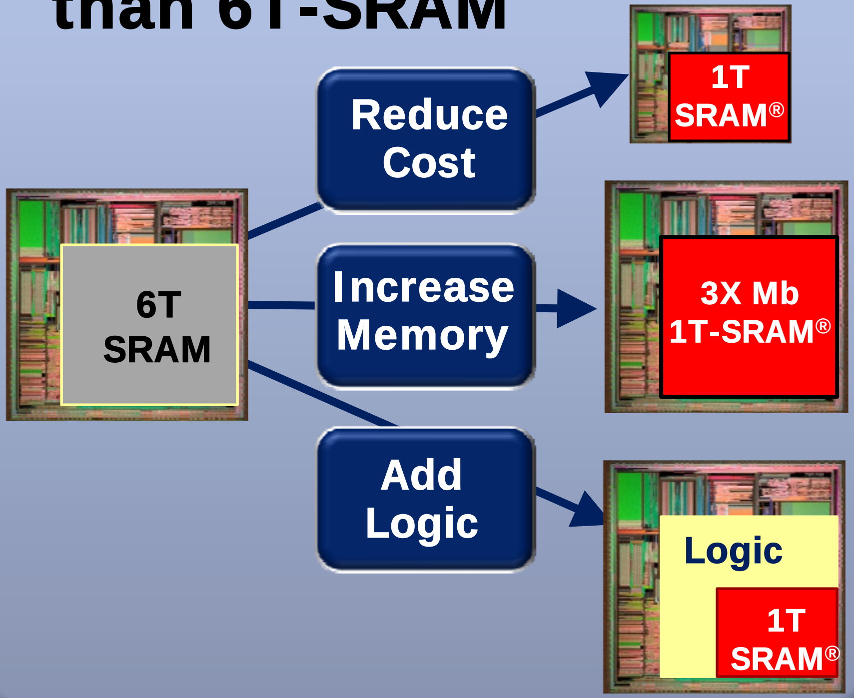
MoSys Foundation Technology

Embedded
1T-SRAM®

Dense
High performance
Portable
Reliable



Up to 3X Denser than 6T-SRAM

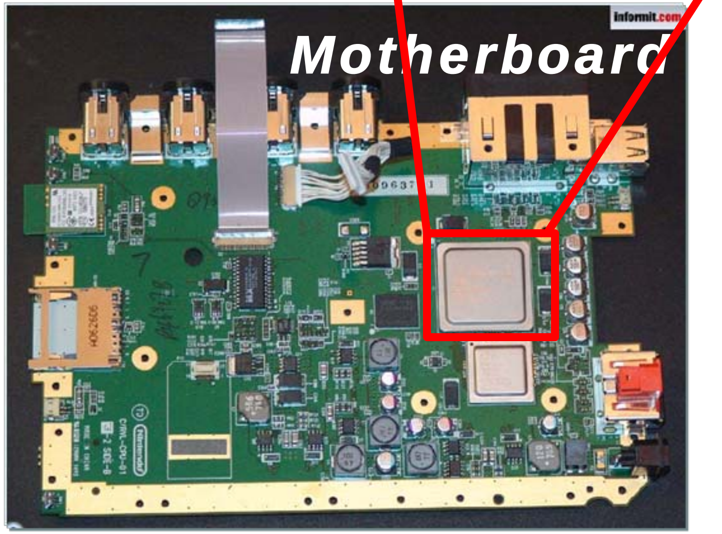


More than 160 million devices shipped

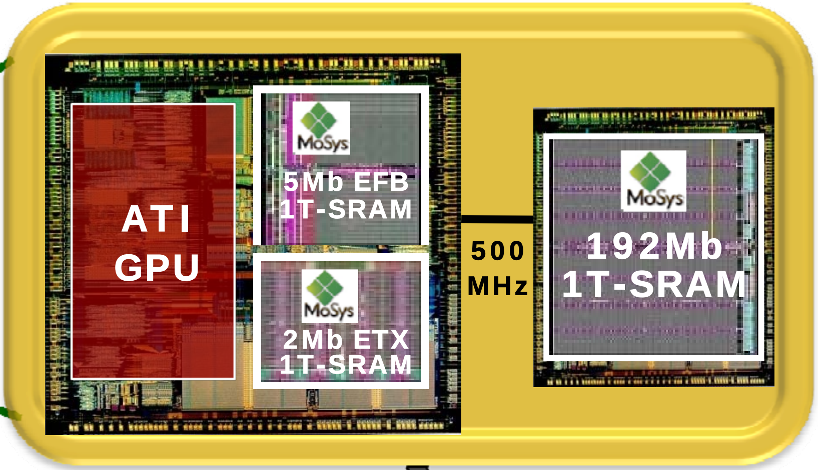
- Game consoles, handsets, networking & consumer devices
- Nintendo Wii™ Proven (NEC chip)

MoSys 1T-SRAM® in Nintendo Wii™

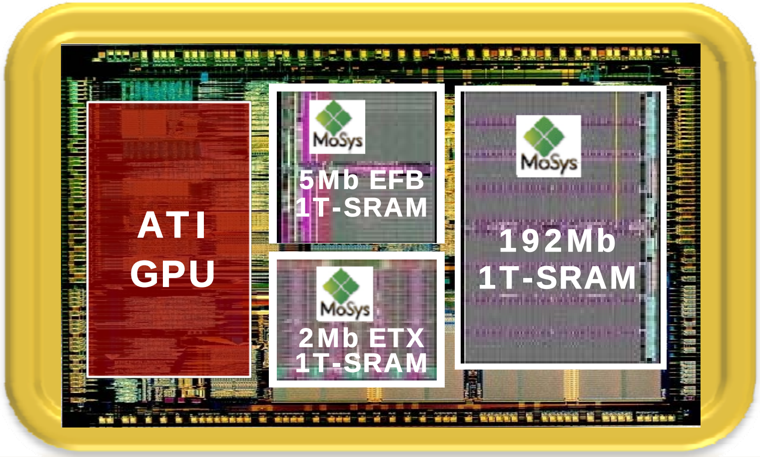
Graphics Processor



90nm – 2 die, MCM



**Next Generation Wii
Cost-down - 1 die**



MoSys Foundation Technology

166 MoSys Patents in Memory and Growing…

2007

- 1 US Patent Filed
- 3 US Patents Granted

2008

- 11 US Patents Filed
- 5 US Patents Granted

MoSys

Customers/Products & Foundry Partners

Foundry/IDMs

1T-SRAM ® Licensees

- tsmc
- NEC
- FUJITSU

- common platform
- Chartered
- UMC
- SMIC
- SilTerra

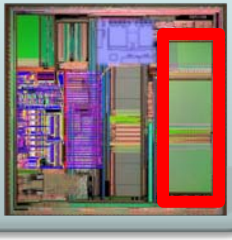
MoSys Growth Strategy

1T-SRAM *for DDI*

Display Driver ICs

Application-specific Solutions

Flagship Patented 1T-SRAM®



Our 1st Application-specific Solution: 1T-SRAM in Display Driver ICs (DDI)

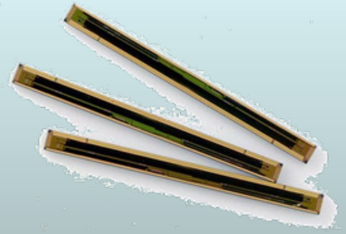
Core Driver is Roadmap
to **Higher Resolution**
Displays

Need MORE
Embedded
Memory

Designs NOW			2010	2012	2012	2013
QVGA 240:320	HVGA 320:480	WVGA 480:864	QHD 540:900	XGA 768:1024	WXGA 800:1280	SXGA 1024:1280
1.32	3.52	9.49	11.12	18.0	23.44	~37-45
Required Memory (Mbits)						

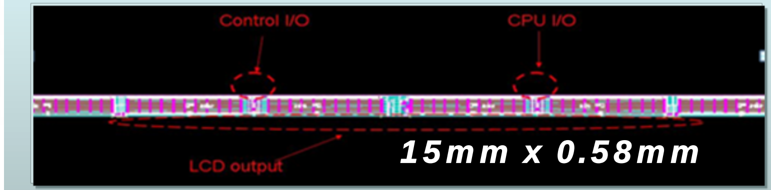
1T-SRAM density advantage = **cost savings**

Need for Short,
Skinny Silicon



Short Skinny Silicon

1T-SRAM is IDEAL



1T-SRAM in Display Driver ICs (DDI) Customer & Market Status

- 1st Customer, LG, starts shipping cell phones with MoSys 1T-SRAM for DDI in 2008

- 4 New Customer Design Wins in 2008
  - 1 HVGA 320:480
  - 1 WQVGA 480:224
  - 2 WVGA 480:864

- Silicon at 3 Foundries at 180nm & 135/130nm

tsmc UMC KeyASIC SilTerra

- Key Growth Opportunity: ~$20M SAM
  - Captive market today – internal 6T solutions
  - Design wins at more DDI companies in 2009
  - New design wins for higher resolution in 2010-2012+
  - Royalties begin to ramp in late 2009

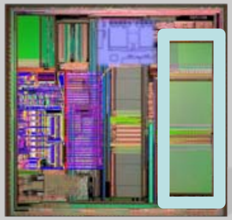
MoSys Growth Strategy

1T-SRAM for DDI

Display Driver ICs

Application-specific Solutions

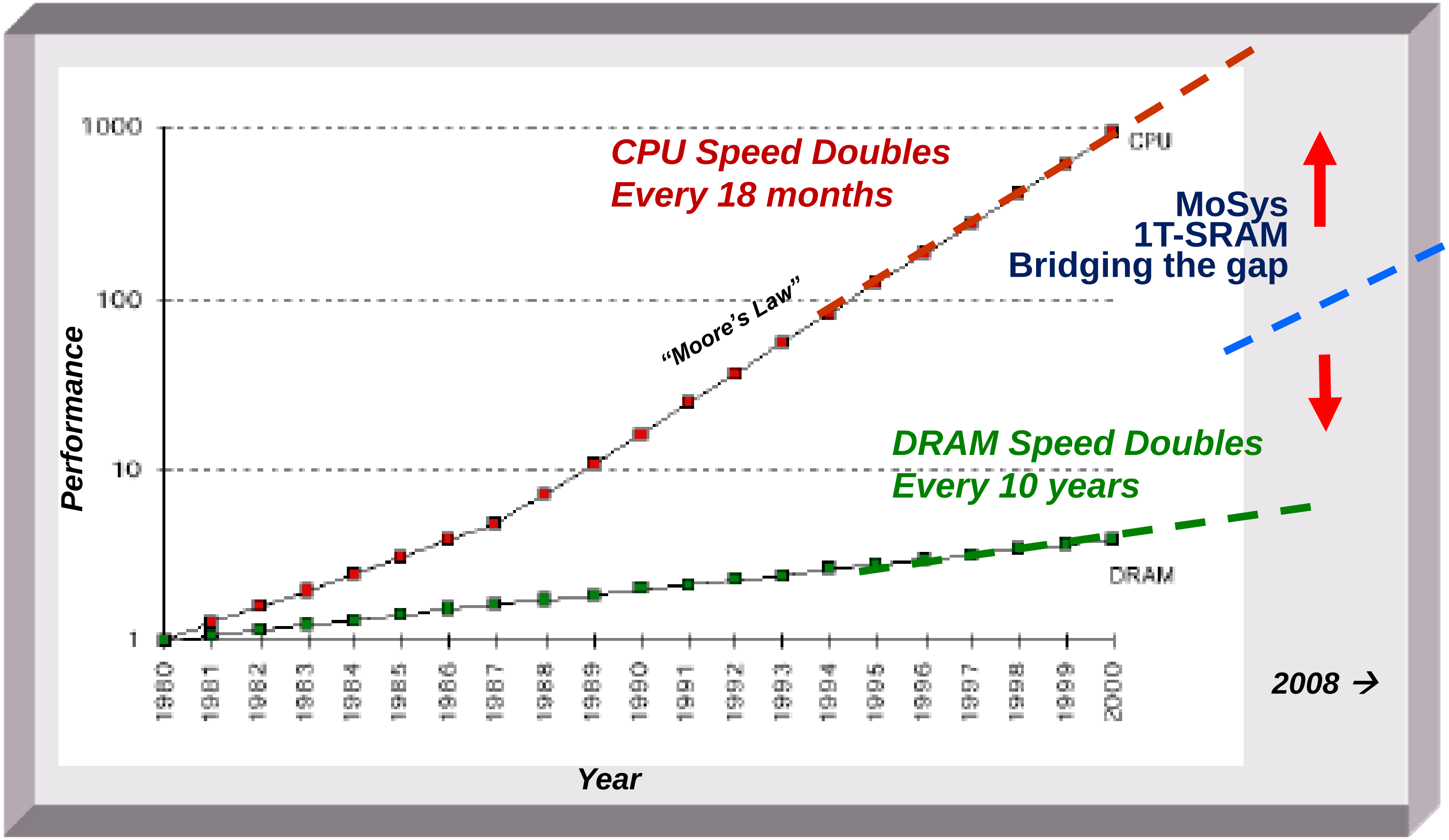
Flagship Patented 1T-SRAM®



Next Generation Technology

High Speed Low Latency Serial Memory

Processor-Memory Performance Gap

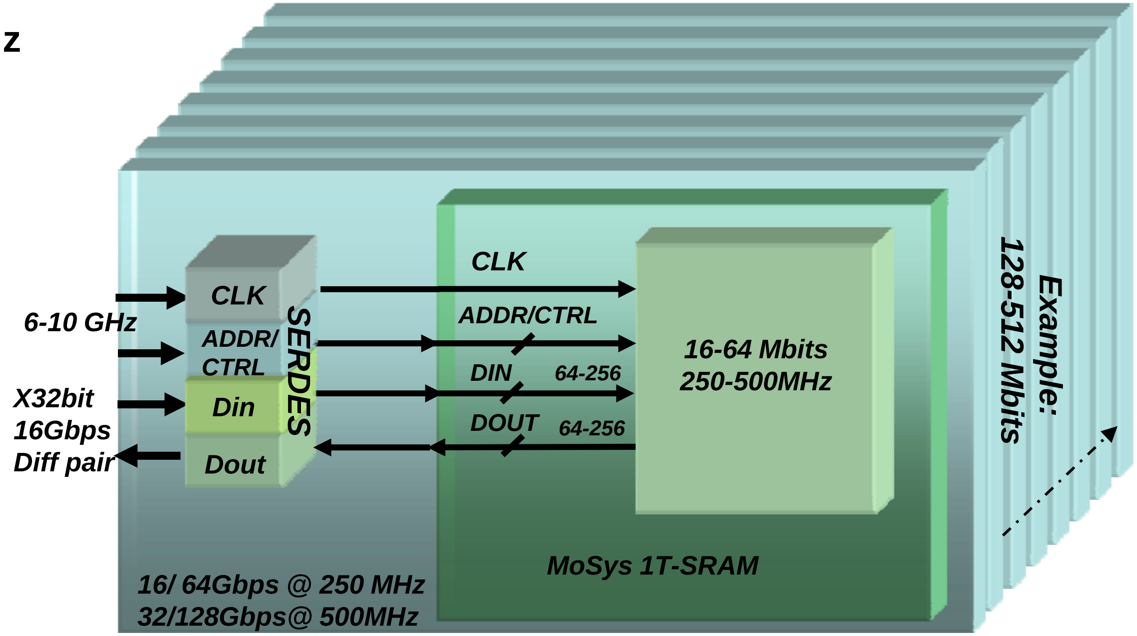


Starting with 1980 performance as a baseline, the performance of memory and CPU over time

Source: www.acm.org

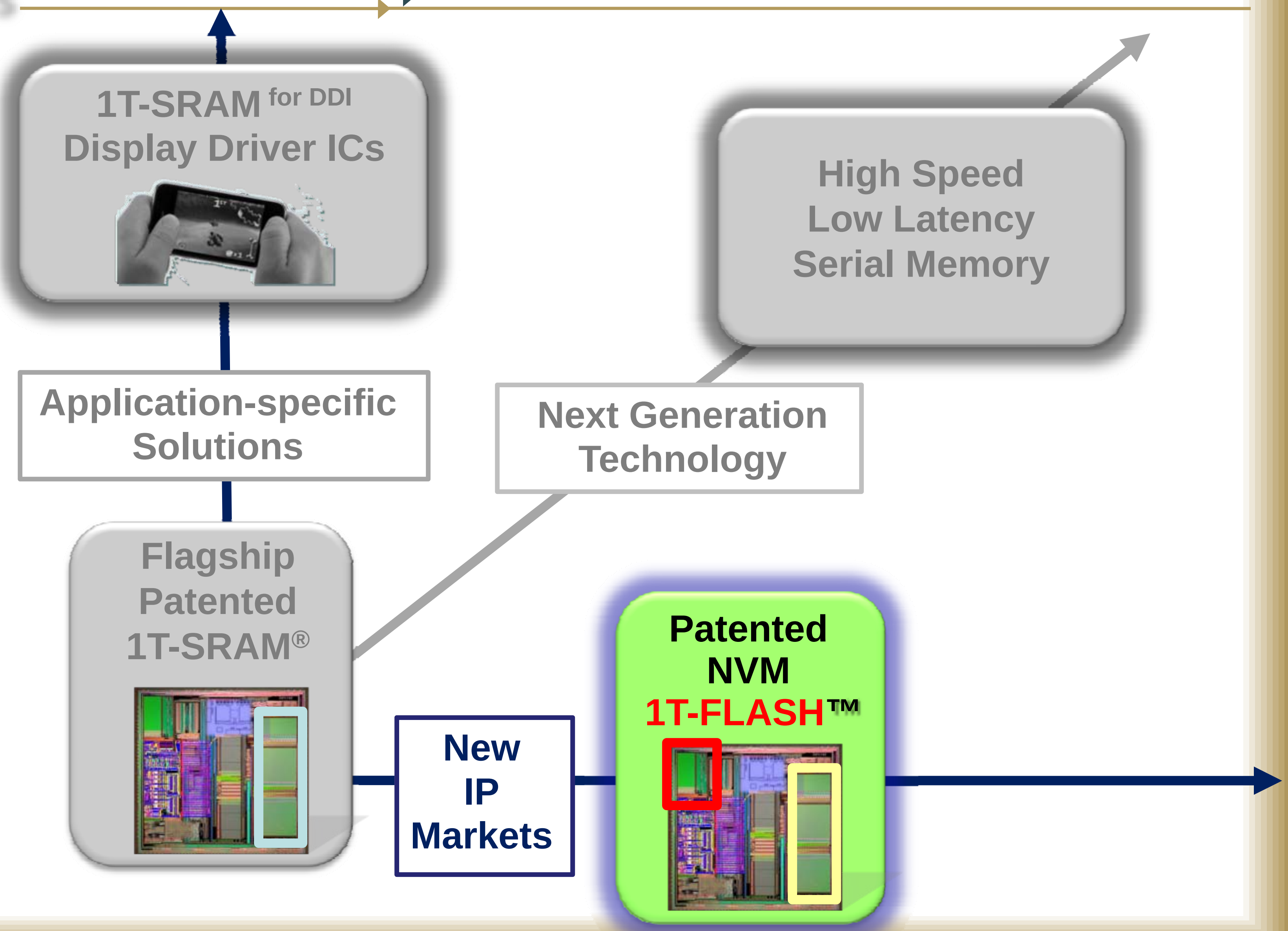
Next Generation High Speed, Low Latency Serial Memory (based on 1T-SRAM)

- Random Access (R/W up to 500MHz)
- Latency:
  - 2 cycles @ 500MHz
  - 1 cycle @ 250MHz
- 64-256 Bit Width
- Single Port
- ECC
- Hard Repair
- 40nmG Process
- Scalable & Cascadable



Target Applications: CPU, GPU, Networking, Graphics
…a New Market Opportunity for MoSys

MoSys Growth Strategy



1T-SRAM for DDI
Display Driver ICs

Application-specific
Solutions

Flagship
Patented
1T-SRAM®

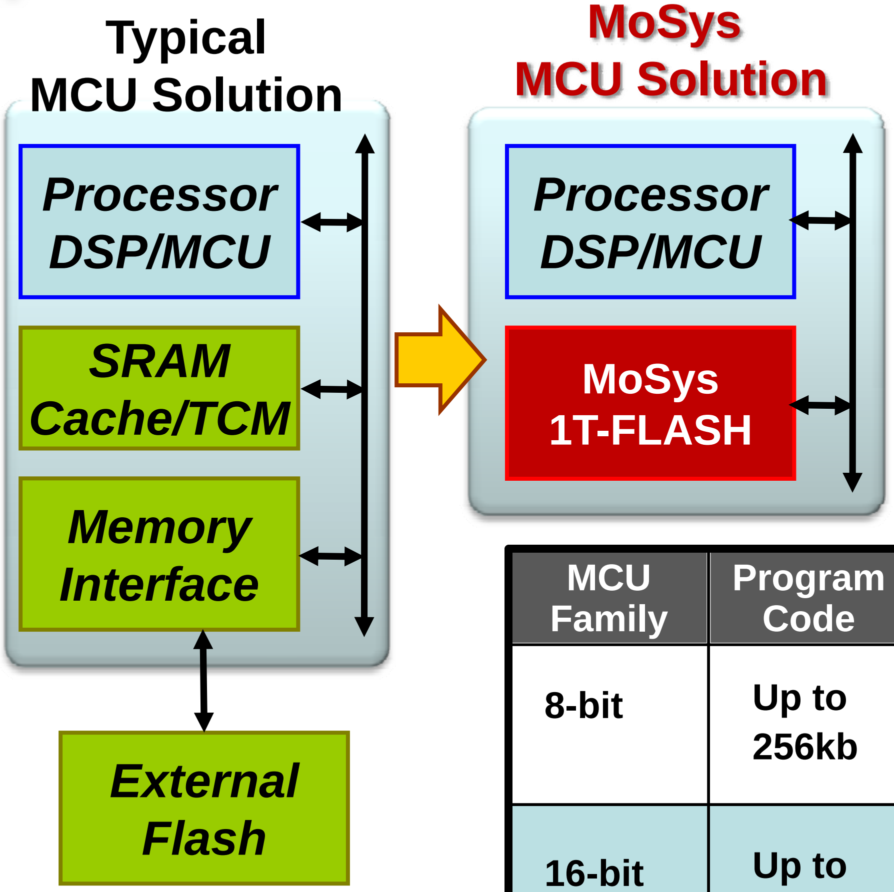
New
IP
Markets

Patented
NVM
1T-FLASH™

Next Generation
Technology

High Speed
Low Latency
Serial Memory

New Embedded NVM 1T-FLASH™ Applications: Programmable Microcontrollers (MCUs)



Typical MCU Solution

Processor DSP/MCU

SRAM Cache/TCM

Memory Interface

External Flash

MoSys MCU Solution

Processor DSP/MCU

MoSys 1T-FLASH

Key Benefits

- Eliminates external Flash
- Program code in NVM
- Reduce I/O number/power
- Improves security

MCU Family	Program Code	Silicon Tech.	Applications
8-bit	Up to 256kb	0.25u	automotive, small home appliances
16-bit	Up to 4Mb	0.25u-0.18u	automotive, industrial, consumer appliances, PCs and peripherals
32-bit	1-16 Mbits	0.13u-90nm & below	digital home consumer, communications, networking, industrial

New Embedded NVM 1T-FLASH™ Technology

- **Key Advantages of MoSys 1T-FLASH™**
  - Performance: 50MHz (130nm) to 200MHz (65nm)
  - Reliable: Built-in TEC Error Correction & Hard Redundancy
  - Scalable: Silicon in .18u, .13u & 65nm at 3 foundries
First-to-market at 65nm

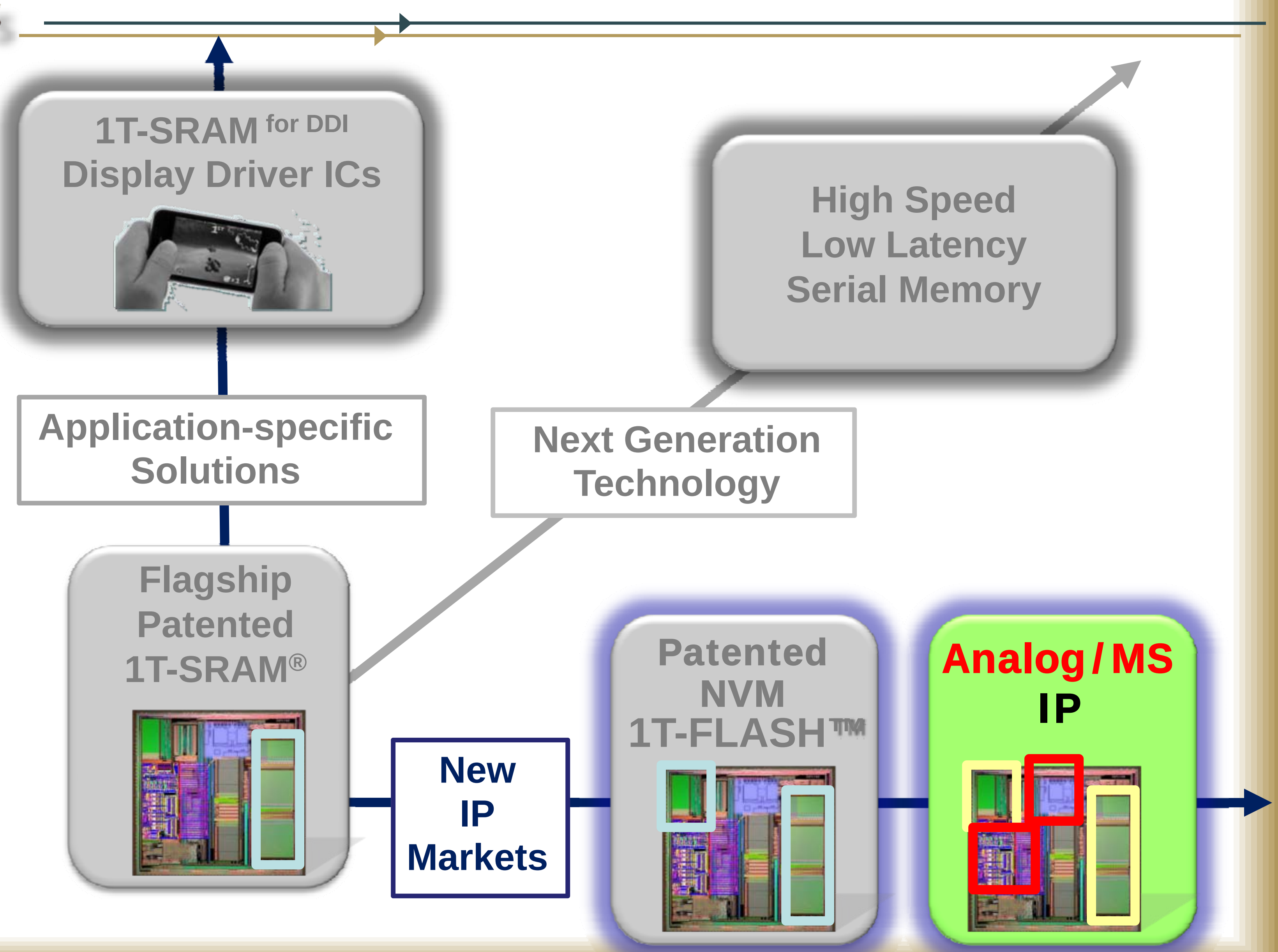
- **Lowest Cost & Risk – standard CMOS Logic Process**
  - *no additional mask steps…*leading competitor uses 8-10 additional masks

- **Other Key Attributes**
  - High Density: 64kb to 64Mbit
  - Data Retention: 10+years at 125C
  - Endurance: 20K cycles

New Embedded NVM 1T-FLASH™ Status

- **Scalable – today silicon in .25, .18, .13u & 65nm at 3 foundries (3.3V & 2.5V)**
  - Developing cell for 40 nm & 32 nm
- **SMIC 130nm**
  - Characterization & qualification complete Q4 2008
- **TSMC 65nm**
  - Taped out October 2008
  - Full qualification Q2 2009
- **Engaged with lead customer developing 32-bit programmable ARM Cortex-based MCU**
  - Their design taped out with our macro (@ SMIC)
  - Prototype production 1QCY(09)

MoSys Growth Strategy



1T-SRAM for DDI
Display Driver ICs

Application-specific Solutions

High Speed
Low Latency
Serial Memory

Next Generation Technology

Flagship
Patented
1T-SRAM®

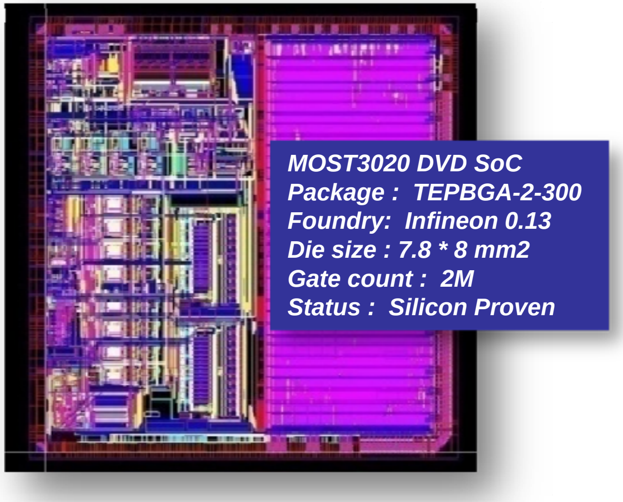
New
IP
Markets

Patented
NVM
1T-FLASH™

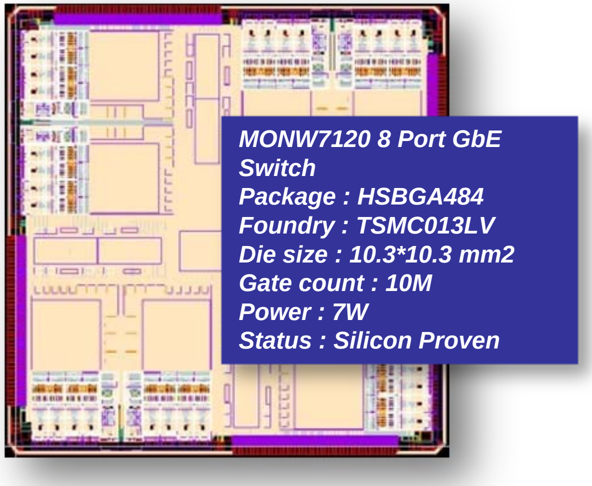
Analog / MS
IP

New Analog/Mixed Signal IP Markets

- **2007 Acquisition of Atmel’s Network Storage Products Group**
  - ~100 hard-to-find analog/mixed-signal & firmware developers
  - core competency & products in Blu-ray & Gigabit Ethernet



MOST3020 DVD SoC
Package : TEPBGA-2-300
Foundry: Infineon 0.13
*Die size : 7.8 * 8 mm2*
Gate count : 2M
Status : Silicon Proven



MONW7120 8 Port GbE Switch
Package : HSBGA484
Foundry : TSMC013LV
*Die size : 10.3*10.3 mm2*
Gate count : 10M
Power : 7W
Status : Silicon Proven

- **Creating silicon-verified, IP solutions for optical storage and high speed networking**
- **Opportunities for new analog/mixed-signal applications**

MoSys Growth Roadmap

- **2008: Flagship 1T-SRAM®: ~$15M, 10%+ Growth**
  - Need for more, high performance/density memory in Pixel (graphics) & Packet (communications) processing

- **New in 2008+: 1T-SRAM$^{\text{for DDI}}$: $20M SAM**
  - Key driver is hi-resolution on small/medium displays
  - 5 design wins today, growth driven by:
    - more customer wins & more design wins at each resolution
    - royalties ramping, starting in late 2009/2010

- **Emerging in 2009+: 1T-FLASH : $200M+ SAM**
  - Key opportunity in Programmable MCU market
  - License revenue will start in 2009, ramp in 2010+
  - Royalty revenue will likely start in 2010+

- **Future Growth Opportunities**
  - Unique application-specific solutions
  - New high speed serial memory program
  - New analog/mixed signal IP markets

Financial Overview

MoSys IP Revenue Model

Customer Design Win

- Customize IP Macro (if not off-the-shelf)
- Customer SoC development and IP integration

Customer ships SoC to Market

- License Revenue
  - NRE – if customized
- License fee
  - Revenue from 17 customers in Q308
  - 11 new projects YTD in 2008 (6 in all of 2007)

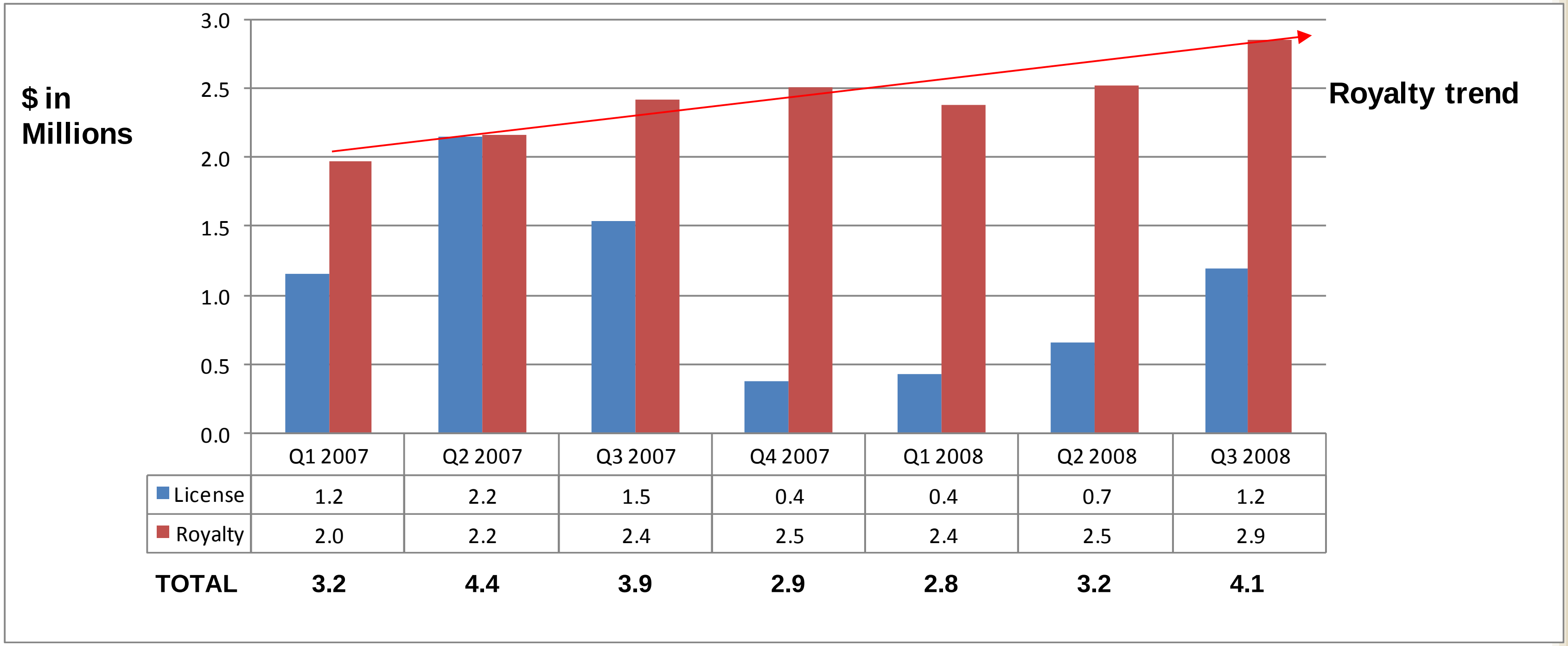
- Royalty revenue
  - 100% margin
  - Revenue from 18 customers in Q308

- Today, gross margins ~80%
- Major focus on building royalty revenue

Financial & Operational Highlights
September 30, 2008

- Q3 Revenue of $4.1 million, + 27% QoQ
    - Reported first revenue from analog/mixed signal business
- YTD revenue of $10.1 million
- Increased royalty revenue 18% year-over-year
- $72 million in cash and investments ($2.2 million cash burn in Q3)
- Booked 4 new orders for 1T-SRAM DDI macros
- Announced Level III & IV qualification on TSMC 90nm G process
- Initiated $5 million stock repurchase plan in October 2008

Revenue Trend



	Q1 2007	Q2 2007	Q3 2007	Q4 2007	Q1 2008	Q2 2008	Q3 2008
🟦 License	1.2	2.2	1.5	0.4	0.4	0.7	1.2
🟥 Royalty	2.0	2.2	2.4	2.5	2.4	2.5	2.9
TOTAL	**3.2**	**4.4**	**3.9**	**2.9**	**2.8**	**3.2**	**4.1**

- ❑ **NEC represented 70% of revenue in 2007; projecting <50% in 2008**
- ❑ **9 new customer wins in 2008, 3 in 2007**
- ❑ **DDI License revenue for 2008 projected >10%; 2007 – none**
- ❑ **Q308 Royalty revenue from pure-play foundry partner doubled**

Summary Income Statement (Non-GAAP*)

(in millions except per share amount)

	YTD 08	Q3 08	Q2 08	Q1 08	Full Year 2007
Total Revenues	$ 10.1	$ 4.1	$ 3.2	$ 2.8	$ 14.3
Licensing	2.3	1.2	0.7	0.4	5.2
Royalty	7.8	2.9	2.5	2.4	9.1
Gross Profit	8.3	3.3	2.5	2.4	12.1
Margin %	*82%*	*82%*	*79%*	*86%*	*85%*
Op Ex	18.1	5.8	6.1	6.3	20.0
Non-GAAP Net Loss	$ (7.9)	$ (2.1)	$ (3.1)	$ (2.8)	$ (3.4)
EPS	$ (0.25)	$ (0.06)	$(0.10)	$(0.09)	$ (0.11)

Non-GAAP: excludes non-cash charges including stock-based compensation, IP R&D and amortization of acquired intangible assets

MoSys: Strong Balance Sheet

	As of September 30, 2008
	Actual (In millions except headcount)
Cash and Investments	**$72.1**
Total Assets	**90.2**
Total Debt	**0**
Stockholders' Equity	**$86.9**
Total Shares Outstanding	**31.9**
Headcount (80%+ is Engineering)	**191**

Summary

- ❑ **Foundation of market leadership in 1T-SRAM**
  - Technology, 166 patents, world class team & customers
- ❑ **Significant new opportunities for growth**
  - Growing demand for flagship 1T-SRAM IP
  - Accelerate growth with ‘application-specific solutions’ - DDI
  - New embedded memory opportunity with 1T-FLASH solution
  - New high speed, low latency Serial Memory
  - New analog/mixed signal IP markets
- ❑ **Strong financial fundamentals**
  - High gross margins with recurring royalty revenue model
  - Strong balance sheet —no debt
- ❑ **New proven management team**

Contacts

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